

## GaAs 공정을 이용한 IMT-Advances System용 전력분배기 설계

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### Design of Power Divider for IMT-Advances System using GaAs Process

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**Abstract :** In this paper, a power divider with a multi-band and broadband are designed and fabricated using an InGaP/GaAs process. The design of this divider is based on multi-band because it is important in the next generation IMT-Advances system. In this design, power divider is fabricated with the frequency of 824 MHz to 894 MHz, 1.8 GHz to 2.2 GHz and 2.3 GHz to 2.4 GHz for cellular, personal communication system (PCS) and Wireless Broadband Internet (WiBro). The topology of the designed power divider is based on the multi-section and fabricated using integrated passive device (IPD) library of nanoENS Inc.. It is measured using network analyzer.

**Key Words :** InGaP/GaAs process, Divider

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